

Efficient and stable photocatalyst for photoelectrochemical splitting of water

Andreas Zerr, Eduard Feldbach, Tavo Romann, Rasmus Seerma, Marco Kirm

▶ To cite this version:

Andreas Zerr, Eduard Feldbach, Tavo Romann, Rasmus Seerma, Marco Kirm. Efficient and stable photocatalyst for photoelectrochemical splitting of water. 8th Baltic Electrochemistry Conference: Finding New Inspiration 2 (BEChem2024), Apr 2024, Tartu, Estonia. hal-04750940

HAL Id: hal-04750940 https://hal.science/hal-04750940v1

Submitted on 24 Oct 2024

HAL is a multi-disciplinary open access archive for the deposit and dissemination of scientific research documents, whether they are published or not. The documents may come from teaching and research institutions in France or abroad, or from public or private research centers.

L'archive ouverte pluridisciplinaire **HAL**, est destinée au dépôt et à la diffusion de documents scientifiques de niveau recherche, publiés ou non, émanant des établissements d'enseignement et de recherche français ou étrangers, des laboratoires publics ou privés.

Efficient and stable photocatalyst for photoelectrochemical splitting of water

Andreas Zerr¹, Eduard Feldbach^{2,*}, Tavo Romann³, Rasmus Seerma², Marco Kirm²

¹LSPM-CNRS, Université Sorbonne Paris Nord, France
²Institute of Physics, University of Tartu, Estonia
³Institute of Chemistry, University of Tartu, Estonia
*eduard.feldbach@ut.ee

The commercialization of photoelectrochemical (PEC) water splitting technology requires an efficient, stable, long service life, low price, and production scalable photocatalyst. Inspired by earlier publications of competing teams and knowledge of the material by the French partner, the project team is synthesizing and investigating the spinel-structured γ -Sn₃N₄, expected to be suitable for the efficient PEC splitting of water. Two synthesis methods were tested. Firstly, the synthesis of microscopic amounts of the oxygen-free γ -Sn₃N₄ via the reaction of elemental tin with molecular nitrogen, $3 \cdot \text{Sn} + 2 \cdot \text{N}_2 \rightarrow \gamma$ -Sn₃N₄, in a laser heated diamond anvil cell (LH-DAC) was successfully accomplished¹. The compound formed at pressures between 15.7 GPa and 20 GPa and temperatures ~2000°C. However, the presence of unreacted tin was recognized even though nitrogen was introduced in excess.

Secondly, RF-magnetron sputtering was applied to deposit films of γ -Sn₃N₄ on various substrates such as monocrystalline Si-wafers, single crystals of spinel-structured MgAl₂O₄, glass- and plastic plates. As followed from the preliminary XRD measurements based on a microfocus source delivering MoKa radiation (IµS high Brilliance-Incoatec Microfocus Source Mo ELM33, Incoatec) and an imaging plate detector (MAR345, marXperts), crystalline products were obtained on the first two substrate types while amorphous products were found on the latter two substrate types. The spatially (~200 µm) resolved XRD examination, performed in LSPM, showed that the phase composition of the crystalline films depends on their thickness. Those of ~160 nm in thickness contained γ -Sn₃N₄ and a presently unknown Sn_xN_y phase (patterns A and B in Figure 1). Also, the films deposited on monocrystalline MgAl₂O₄ exhibited a better crystallinity when compared with those on the monocrystalline Si-wafers. Thick films of ~1.3 µm contained the unknown Sn_xN_y only (patterns C and D in Figure 1), independent of the substrate.

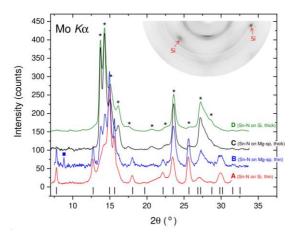


Figure 1: XRD patterns of thin (A, B) and thick (C, D) crystalline films. Vertical ticks indicate positions of the γ -Sn₃N₄ peaks. Stars indicate peaks of an unknown Sn_xN_y phase while a square the (111) peak of MgAl₂O₄, the substrate material. The insert shows the 2D-XRD pattern of the thin film deposited on a monocrystalline Si-wafer.

Acknowledgements

This work was partially supported by the "PHC PARROT" programme (project number: 48994YJ), funded by the French Ministry for Europe and Foreign Affairs, the French Ministry for Higher Education and Research and the Estonian Research Council. The financial support from the Estonian Center of Excellence (TK210) by the Estonian Ministry of Education and Research is gratefully acknowledged.

References

¹Zerr A., Miehe G. *Phil. Trans. R. Soc. A* 381, 20220330 (2023) doi: 10.1098/rsta.2022.0330